

Prospective Data  
**Insulated Gate Bi-Polar Transistor**  
 Type T0900DF65A

**Absolute Maximum Ratings**

	VOLTAGE RATINGS	MAXIMUM LIMITS	UNITS
V <sub>CES</sub>	Collector – emitter voltage	6500	V
V <sub>CES</sub>	Collector – emitter voltage (T <sub>j</sub> 25°C)	6500	V
V <sub>CES</sub>	Collector – emitter voltage (T <sub>j</sub> -40°C)	6000	V
V <sub>DC link</sub>	Permanent DC voltage for 100 FIT failure rate.	3600	V
V <sub>GES</sub>	Peak gate – emitter voltage	±20	V

	RATINGS	MAXIMUM LIMITS	UNITS
I <sub>C</sub>	DC collector current, IGBT	900	A
I <sub>CRM</sub>	Repetitive peak collector current, t <sub>p</sub> =1ms, IGBT	1800	A
I <sub>F(DC)</sub>	Continuous DC forward current, Diode	900	A
I <sub>FRM</sub>	Repetitive peak forward current, t <sub>p</sub> =1ms, Diode	1800	A
I <sub>FSM</sub>	Peak non-repetitive surge t <sub>p</sub> =10ms, V <sub>RM</sub> =60%V <sub>RRM</sub> , Diode (Note 4)	7590	A
I <sub>FSM2</sub>	Peak non-repetitive surge t <sub>p</sub> =10ms, V <sub>RM</sub> ≤10V, Diode (Note 4)	8350	A
P <sub>MAX</sub>	Maximum power dissipation, IGBT (Note 2)	10.6	KW
(di/dt) <sub>cr</sub>	Critical diode di/dt (note 3)	3000	A/μs
T <sub>j</sub>	Operating temperature range.	-40 to +125	°C
T <sub>stg</sub>	Storage temperature range.	-40 to +125	°C

Notes: -

- 1) Unless otherwise indicated T<sub>j</sub> = 125°C.
- 2) T<sub>sink</sub> = 25°C, double side cooled.
- 3) Maximum commutation loop inductance 300nH.
- 4) Half-sinewave, 125°C T<sub>j</sub> initial.

## Characteristics

### IGBT Characteristics

	PARAMETER	MIN	TYP	MAX	TEST CONDITIONS	UNITS
V <sub>CE(sat)</sub>	Collector – emitter saturation voltage	-	3.6	-	I <sub>C</sub> = 900A, V <sub>GE</sub> = 15V, T <sub>j</sub> = 25°C	V
		4.4	4.8	5.2	I <sub>C</sub> = 900A, V <sub>GE</sub> = 15V	V
V <sub>T0</sub>	Threshold voltage	-	-	2.49	Current range: 300A – 900A	V
r <sub>T</sub>	Slope resistance	-	-	3.02		mΩ
V <sub>GE(TH)</sub>	Gate threshold voltage	-	5.2	-	V <sub>CE</sub> = V <sub>GE</sub> , I <sub>C</sub> = 900mA	V
I <sub>CES</sub>	Collector – emitter cut-off current	-	10	35	V <sub>CE</sub> = V <sub>CES</sub> , V <sub>GE</sub> = 0V	mA
I <sub>GES</sub>	Gate leakage current	-	-	40	V <sub>GE</sub> = ±20V	µA
C <sub>ies</sub>	Input capacitance	-	160	-	V <sub>CE</sub> = 10V, V <sub>GE</sub> = 0V, f = 100kHz, T <sub>j</sub> =25°C	nF
t <sub>d(on)</sub>	Turn-on delay time	-	2.1	-	I <sub>C</sub> = 900A, V <sub>CE</sub> = 3600V, di/dt = 2500A/µs	µs
t <sub>r(V)</sub>	Rise time	-	2.5	-		µs
Q <sub>g(on)</sub>	Turn-on gate charge	-	5	-	V <sub>GE</sub> = ±15V, L <sub>s</sub> = 300nH	µC
E <sub>on</sub>	Turn-on energy	-	6.3	-	R <sub>g(ON)</sub> = 3.3Ω, R <sub>g(OFF)</sub> = 11Ω, C <sub>GE</sub> = 68nF	J
t <sub>d(off)</sub>	Turn-off delay time	-	4.3	-	Integral diode used as freewheel diode (Note 3 & 4)	µs
t <sub>f(l)</sub>	Fall time	-	2.3	-		µs
Q <sub>g(off)</sub>	Turn-off gate charge	-	5.5	-		µC
E <sub>off</sub>	Turn-off energy	-	5.1	-		J
I <sub>SC</sub>	Short circuit current	-	4900	-	V <sub>GE</sub> = +15V, V <sub>CC</sub> = 3600V, V <sub>CEmax</sub> ≤ V <sub>CES</sub> , t <sub>p</sub> ≤ 10µs	A

### Diode Characteristics

	PARAMETER	MIN	TYP	MAX	TEST CONDITIONS	UNITS
V <sub>F</sub>	Forward voltage	-	3	-	I <sub>F</sub> = 900A, T <sub>j</sub> = 25°C	V
		-	3.4	3.8	I <sub>F</sub> = 900A	V
V <sub>T0</sub>	Threshold voltage	-	-	1.89	Current range 300A – 900A	V
r <sub>T</sub>	Slope resistance	-	-	2.12		mΩ
I <sub>rm</sub>	Peak reverse recovery current	-	950	-	I <sub>F</sub> = 900A, V <sub>GE</sub> = -15V, di/dt = 2500A/µs	A
Q <sub>rr</sub>	Recovered charge	-	1500	-		µC
t <sub>rr</sub>	Reverse recovery time, 50% chord	-	1.2	-		µs
E <sub>r</sub>	Reverse recovery energy	-	2.2	-		J

### Thermal Characteristics

	PARAMETER	MIN	TYP	MAX	TEST CONDITIONS	UNITS
R <sub>thJK</sub>	Thermal resistance junction to sink, IGBT	-	-	9.4	Double side cooled	K/kW
		-	-	14.3	Collector side cooled	K/kW
		-	-	27.6	Emitter side cooled	K/kW
R <sub>thJK</sub>	Thermal resistance junction to sink, Diode	-	-	16	Double side cooled	K/kW
		-	-	23.4	Cathode side cooled	K/kW
		-	-	50.6	Anode side cooled	K/kW
F	Mounting force	45	-	55	Note 2	kN
W <sub>t</sub>	Weight	-	2.2	-		g

Notes:-

- 1) Unless otherwise indicated T<sub>j</sub> = 125°C.
- 2) Consult application note 2008AN01 for detailed mounting requirements
- 3) C<sub>GE</sub> is additional gate – emitter capacitance added to output of gate drive
- 4) Figures 6 to 9 are obtained using integral diode as freewheeling diode

**Curves**

Figure 1 – Typical collector-emitter saturation voltage characteristics

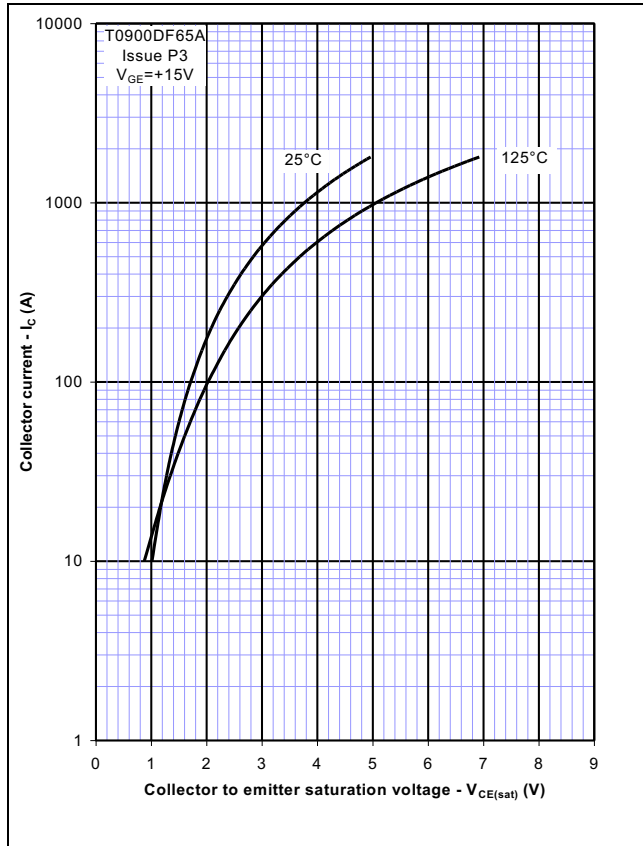


Figure 2 – Typical output characteristic

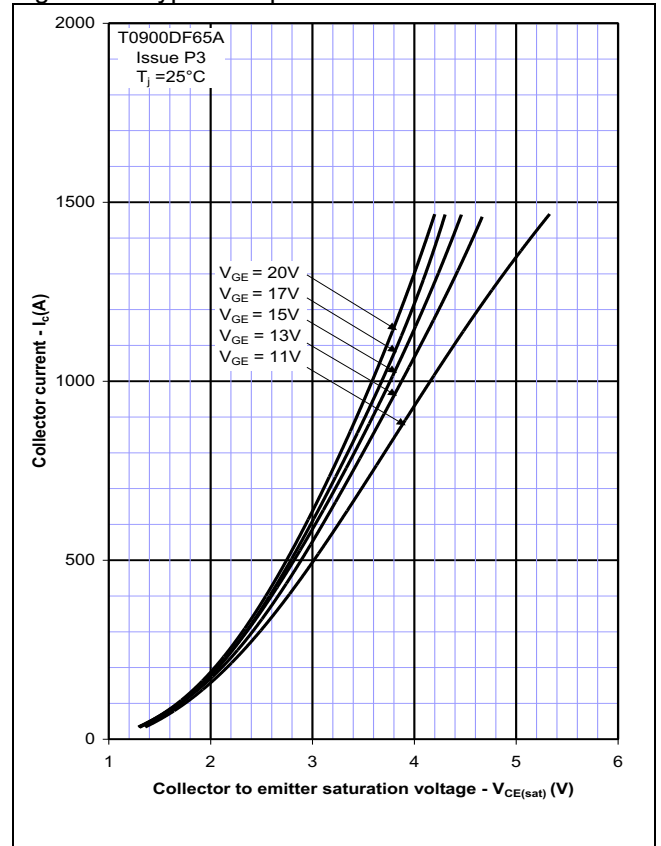


Figure 3 – Typical output characteristic

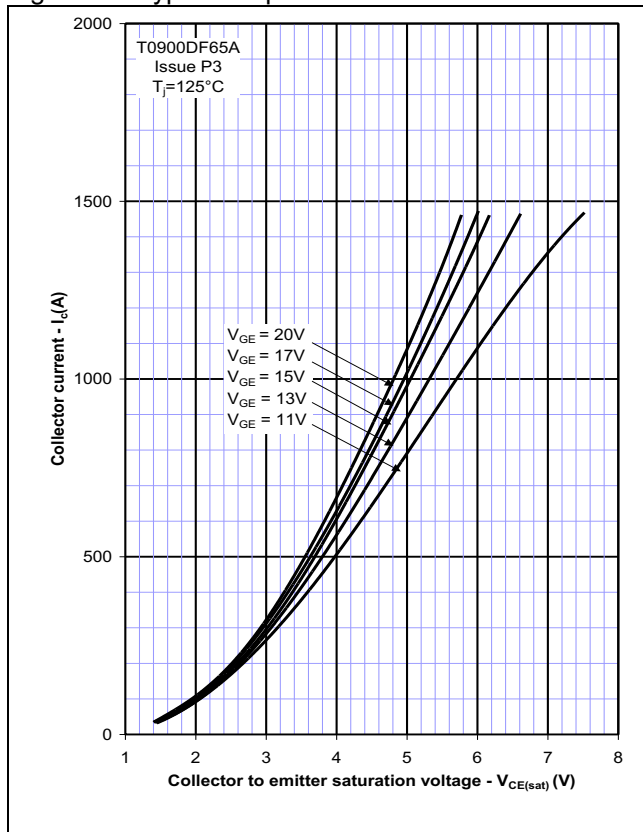


Figure 4 – Typical turn-on delay time vs gate resistance

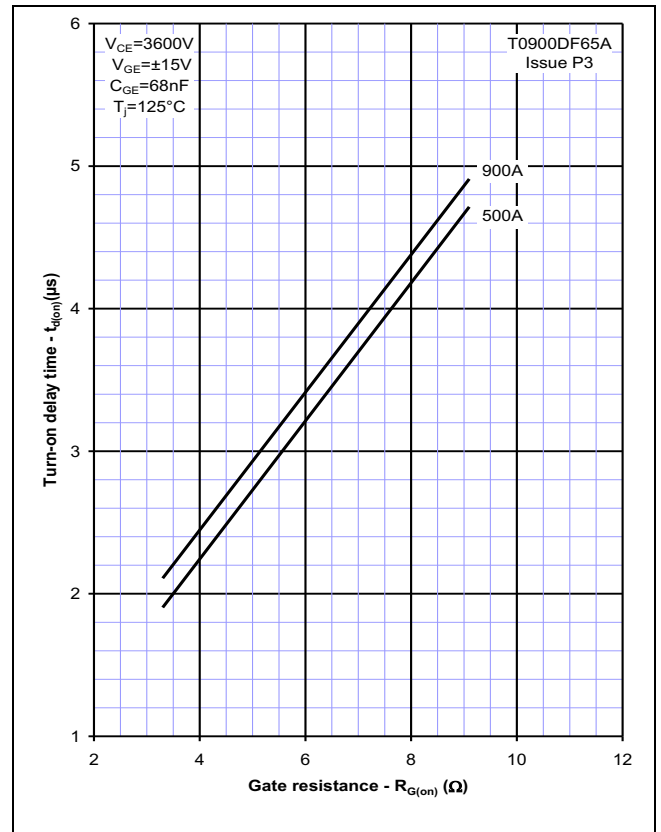


Figure 5 – Typical turn-off delay time vs. gate resistance

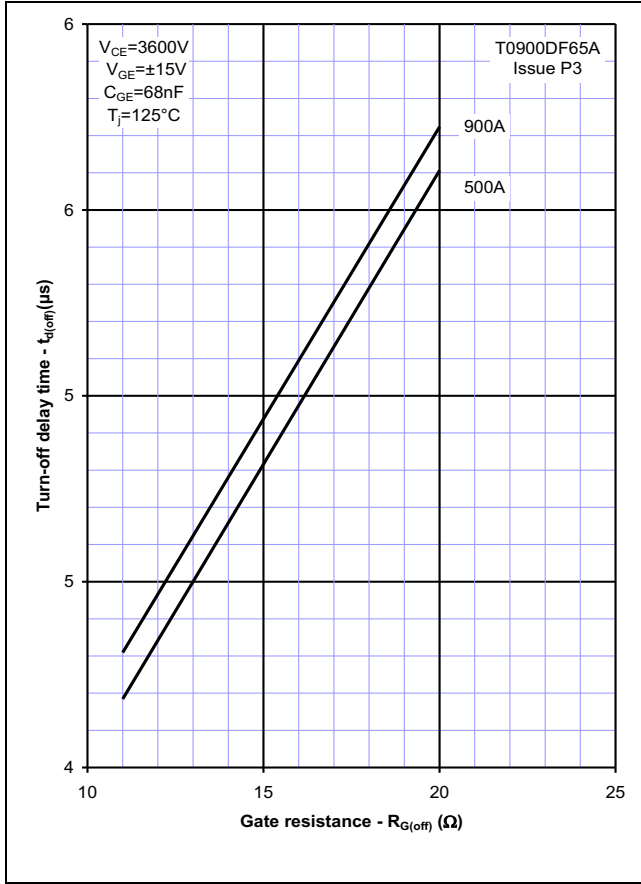


Figure 6 – Typical turn-on energy vs. collector current

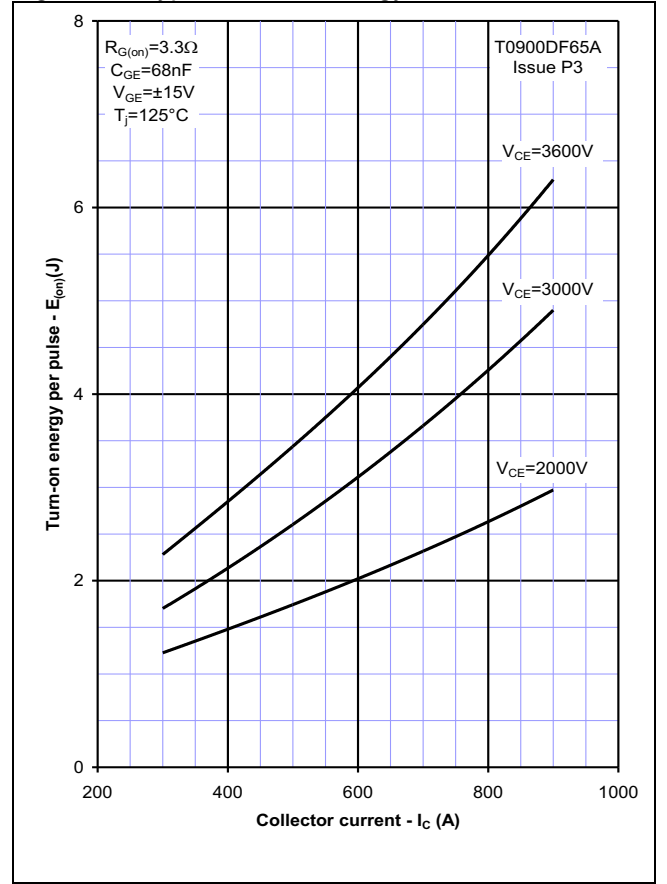


Figure 7 – Typical turn-on energy vs. di/dt

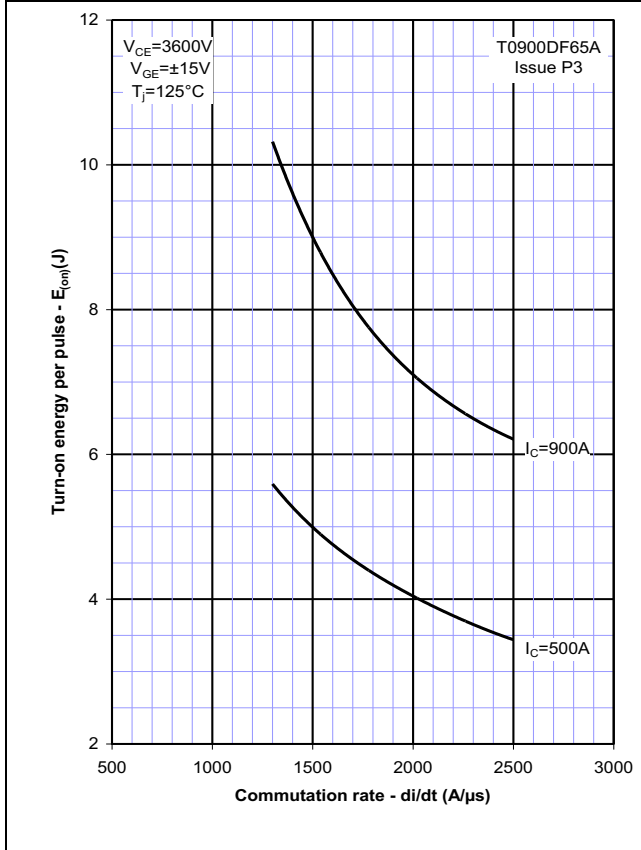


Figure 8 – Typical turn-off energy vs. collector current

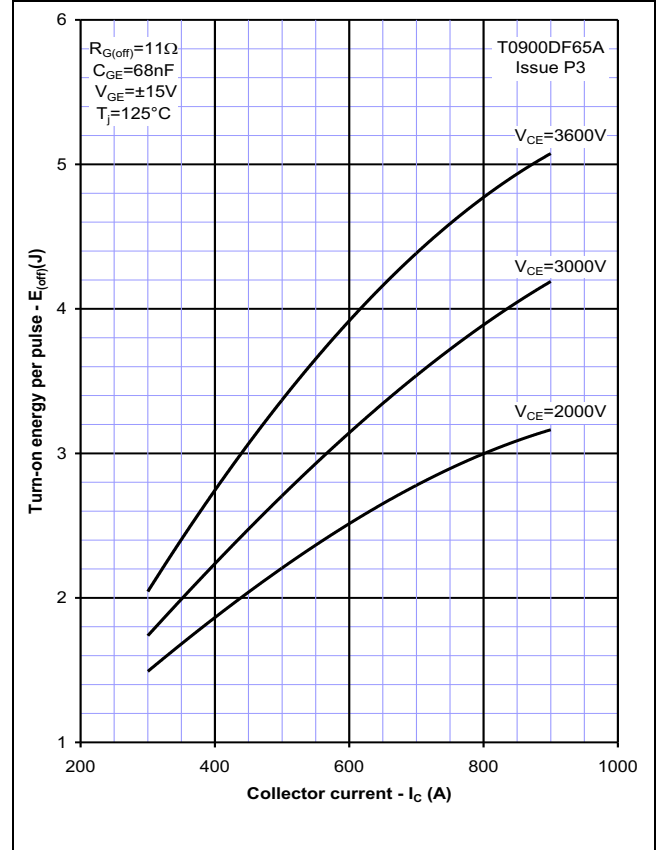


Figure 9 – Turn-off energy vs voltage

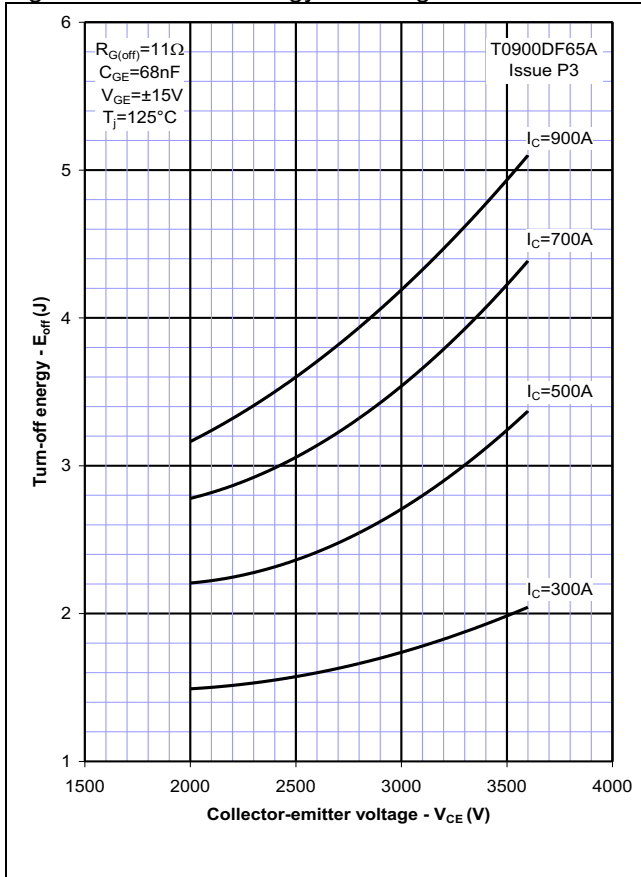


Figure 10 – Safe operating area (IGBT)

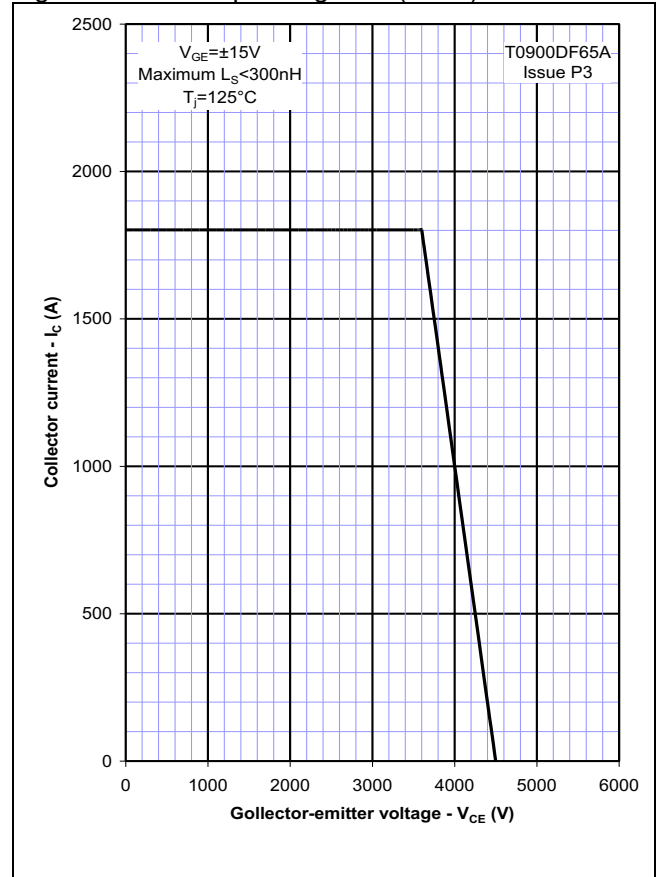


Figure 11 – Typical diode forward characteristics

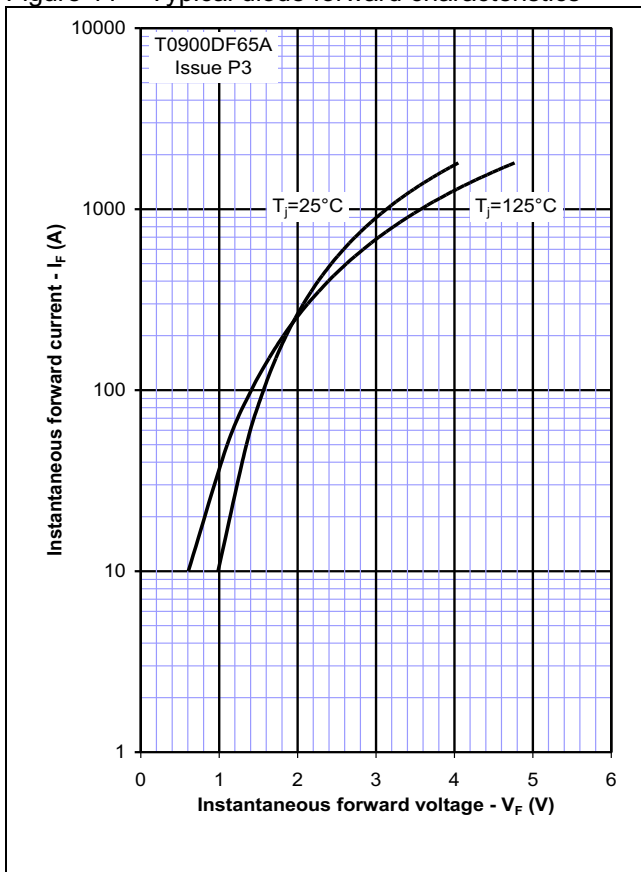


Figure 12 – Typical recovered charge

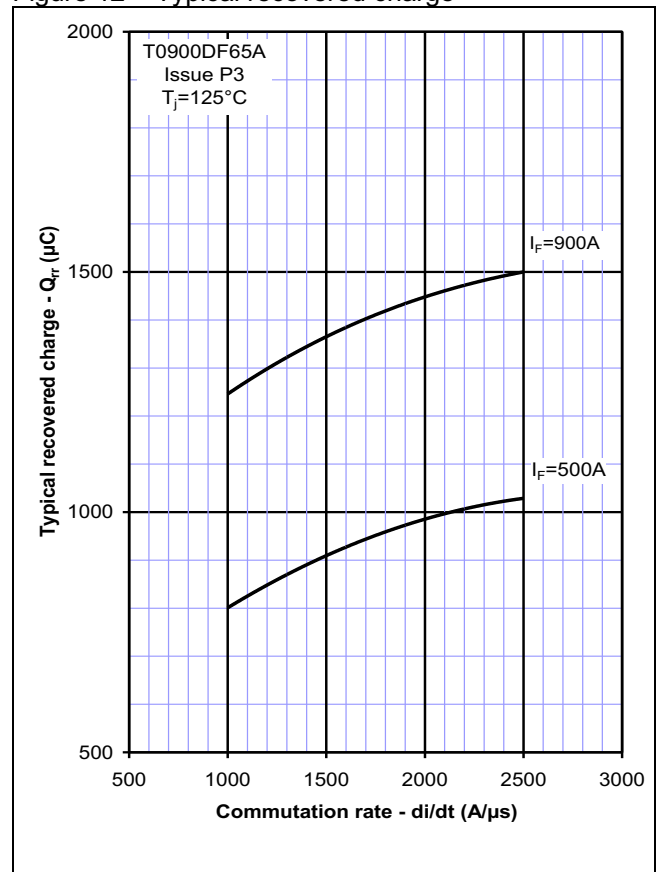


Figure 13 – Typical reverse recovery current

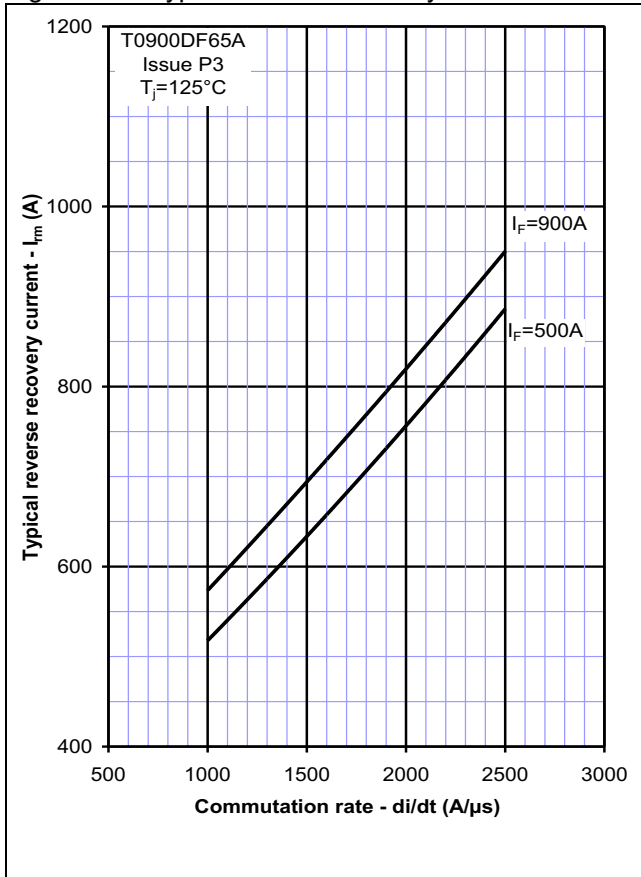


Figure 14 – Typical reverse recovery time

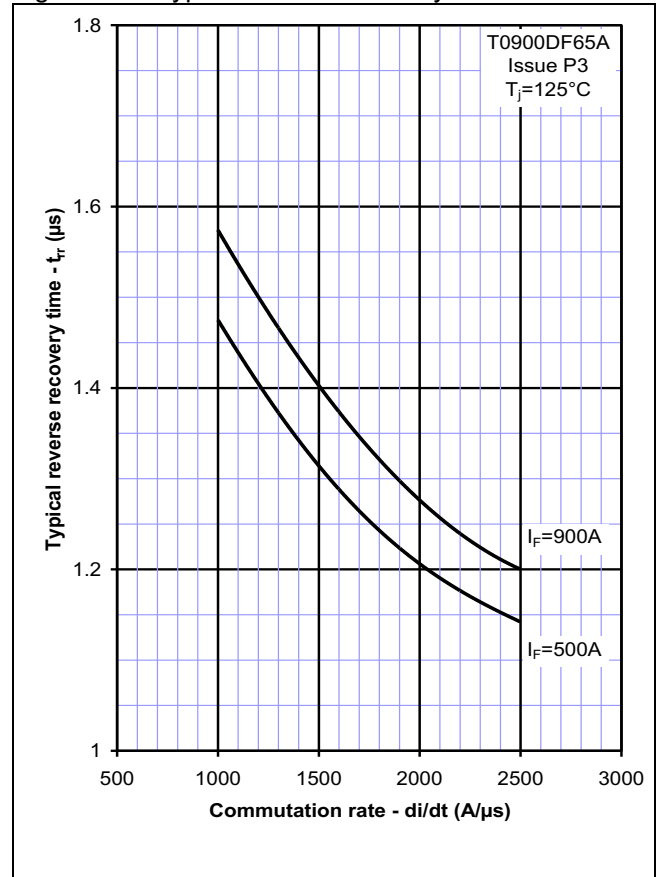


Figure 15 – Typical reverse recovery energy

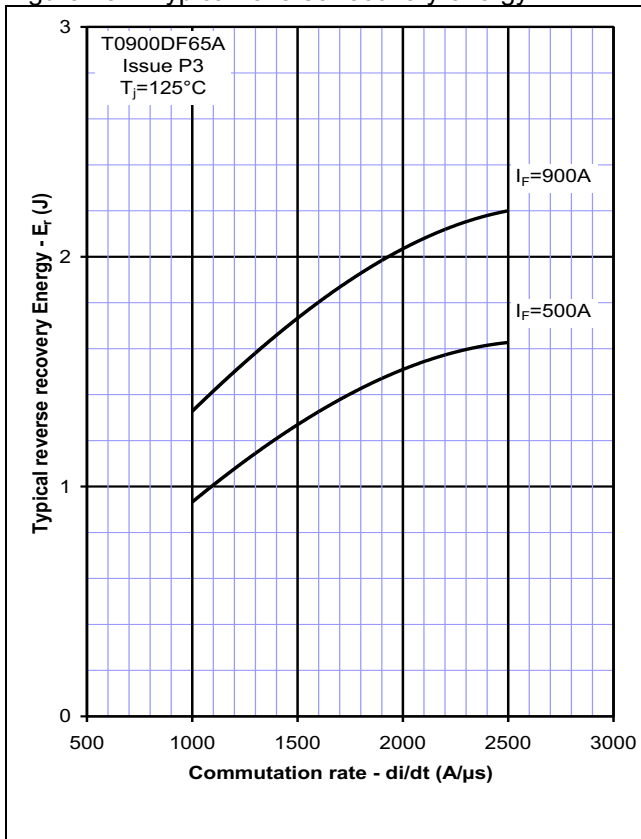


Figure 16 – Safe operating area (Diode)

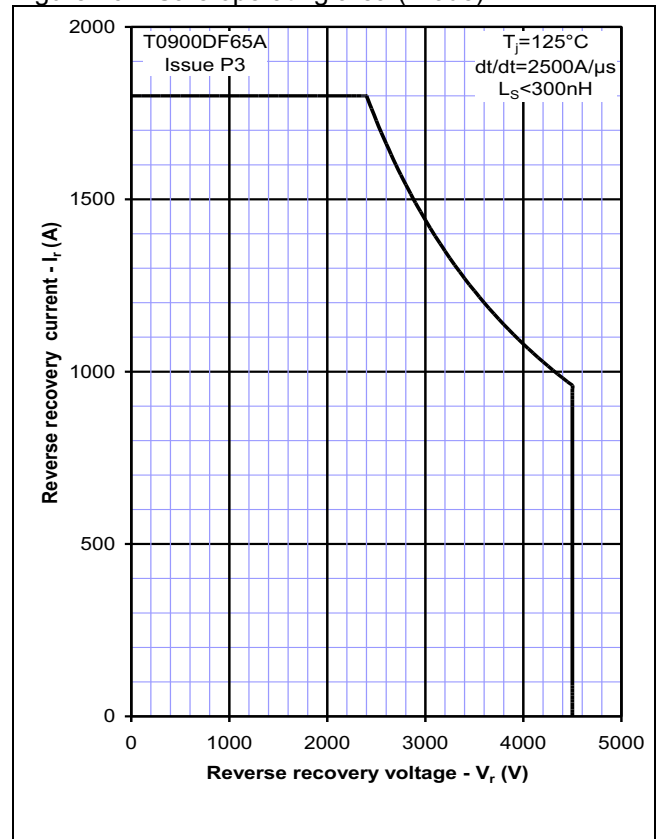


Figure 17 – Transient thermal impedance (IGBT)

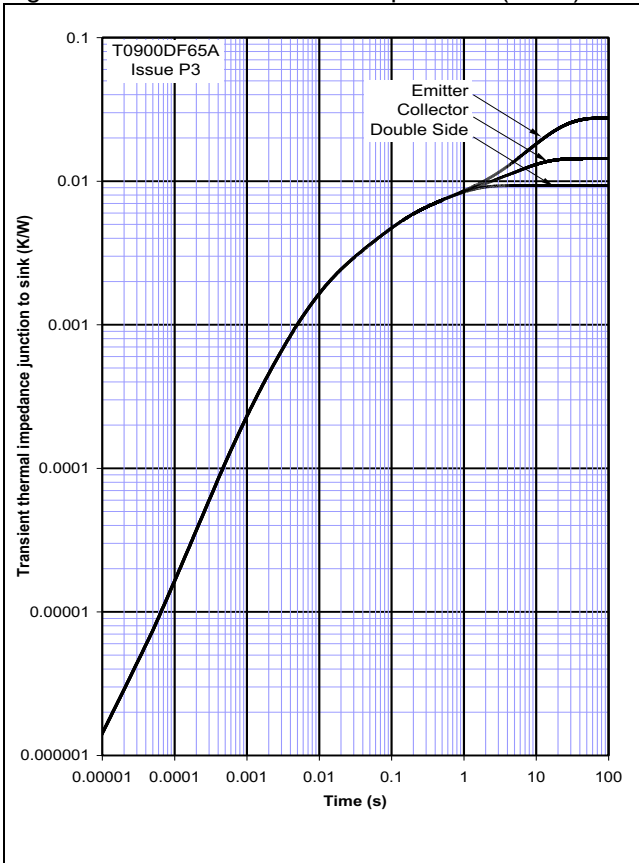
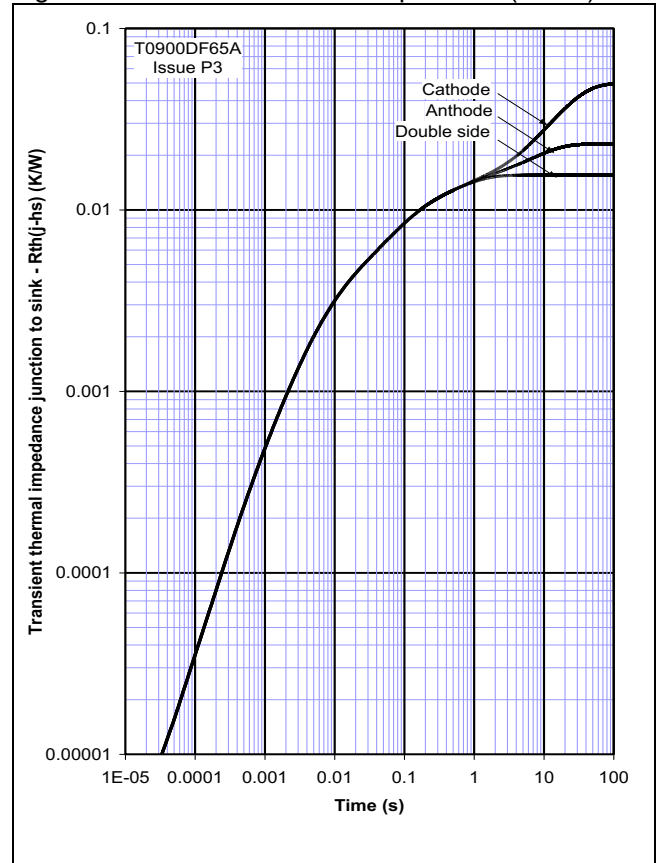


Figure 18 – Transient thermal impedance (Diode)









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